

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Fonash et al.

Serial No.: 09/836,449

Filed: April 17, 2001

For: DEPOSITED THIN FILMS AND THEIR USE IN SEPARATION AND
SACRIFICIAL LAYER APPLICATIONS

Examiner: Not Yet Assigned

Art Unit: 1771

Docket No.: 823.0052USQ1

Commissioner for Patents
Washington, D.C. 20231



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INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with applicant's duty of disclosure under 37 C.F.R. §1.56, please find attached hereto form PTO-1449 listing information which may be material to the patentability of this application. This Information Disclosure Statement is being filed:

_____ Within three (3) months of the filing date of the national application;

_____ Within three (3) months of the date of entry of the national stage as set forth in 37 C.F.R. §1.491 in an international application;

XXX Before the mailing date of a first Office Action on the merits;

_____ After the filing date or date of first Office Action, but before the mailing date of a final action under 37 C.F.R. §1.113, provided that this occurs prior to the issuance of a Notice of Allowance and provided that this I.D.S. is accompanied by either a certification as specified in 37 C.F.R. §1.97(e) or the fee set forth in 37 C.F.R. §1.17(p);

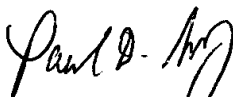
— After the filing date or date of first Office Action, but before the mailing date of a Notice of Allowance under 37 C.F.R. §1.311, provided that this occurs prior to the final action and provided that this I.D.S. is accompanied by either a certification as specified in 37 C.F.R. §1.97(e) or the fee set forth in 37 C.F.R. §1.17(p);

— After the mailing date of a final action under 37 C.F.R. §1.113, provided that this occurs prior to the issuance of a Notice of Allowance and provided that this I.D.S. is accompanied by either a certification as specified in 37 C.F.R. §1.97(e), a petition requesting consideration of the I.D.S., and the petition fee set forth in 37 C.F.R. §1.17(i)(1); and

— After the mailing date of a Notice of Allowance under 37 C.F.R. §1.311, provided that this occurs prior to the issuance of a final action and provided that this I.D.S. is accompanied by either a certification as specified in 37 C.F.R. §1.97(e), a petition requesting consideration of the I.D.S., and the petition fee set forth in 37 C.F.R. §1.17(i)(1).

It should be understood that attention has been called to the references that have been deemed to be pertinent to the claimed present invention. In concluding what was pertinent, the criteria employed was considered most appropriate in light of the invention shown in the present application. However, the Examiner or others may deem some other criteria to be just as appropriate or more appropriate. Therefore, the Examiner is respectfully urged to review the listed references and to make the usual careful independent search for other prior art that may be pertinent.

Respectfully submitted,



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FORM PTO-1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)

823.0052USQ1

Application Number

09/836,449

Applicant

Fonash et al.

Filing Date

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Group Art Unit

1771

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U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,288,390	9/11/01	Siuzdak et al.	250	288	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)

✓	Kim et al. "Thin-Film Micromirror Array." <i>Information Display 4 & 5/99</i> , 30-33.
✓	Yonehara et al. "ELTRAN; SOI-Epi Wafer by Epitaxial Layer Transfer from Pouous Si." ELTRAN Business Center, Canon, Inc., Abstract No. 438.
✓	Stern et al. "Nanochannel fabrication for chemical sensors." <i>J. Vac. Sci. Technol.</i> 15(6), Nov/Dec 1997, 2887-2891.
✓	Turner et al. "Monolithic Fabrication of Nanofluidic Artificial Gel Media for DNA Electrophoresis." <i>SPIE Vol.</i> 3258, 114-121.
✓	French. "Development of surface micromachining techniques compatible with on-chip electronics." <i>J. Micromech. Microeng.</i> (1996) 197-211.
✓	Sugiyama et al. "Micromachined sensors using polysilicon sacrificial layer etching technology." <i>IEDM Tech. Dig.</i> , (1994) 127-130.
✓	Bell et al. "Porous silicon as a sacrificial material." <i>J. Micromech. Microeng.</i> 6 (1996) 361-369.
✓	Steiner et al. "Using porous silicon as a sacrificial layer." <i>J. Micromech. Microeng.</i> 3 (1993) 32-36.
✓	Boer et al. "Micromachining of buried micro channels in silicon." <i>J. Micromech. Systems</i> , Vol. 9, No. 1, March 2000, 94-103.
✓	Uhlir, Jr. "Electrolytic shaping of Germanium and Silicon." <i>The Bell System Technical Journal</i> . March 1956. 333-347.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

